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## Correction: Effects of pressure and temperature on topological electronic materials $X_2Y_3$ ( $X = \text{As, Sb, Bi}$ ; $Y = \text{Se, Te}$ ) using first-principles

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Correction for 'Effects of pressure and temperature on topological electronic materials  $X_2Y_3$  ( $X = \text{As, Sb, Bi}$ ;  $Y = \text{Se, Te}$ ) using first-principles' by Le Fang *et al.*, *Phys. Chem. Chem. Phys.*, 2023, **25**, 20969–20978, <https://doi.org/10.1039/D3CP01951A>.

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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